

IN THE CLAIMS:

Please cancel non-elected claims 5 to 13, without prejudice.

Please add new claims 15 and 16.

A complete listing of all the claims is presented as follows:

Claim 1. (Currently Amended).

A process for producing a silicon single crystal, comprising pulling a silicon single crystal from a silicon melt which is contained in a crucible having a crucible wall and having a crucible diameter of at least 450 mm,

placing a heat shield above said crucible; and said silicon single crystal being pulled with a diameter of at least 200 mm; and

exposing the silicon melt to an influence of a traveling magnetic field which exerts a substantially vertically oriented force on the melt in a region of the crucible wall,

~~said traveling magnetic field being the single type of magnetic field which is applied to the melt.~~

except for said traveling magnetic field no further magnetic field being applied to the melt.

Claim 2. (Original).

The process as claimed in claim 1,
wherein the silicon single crystal is pulled with an oxygen
concentration of at least $5 * 10^{17}$ atoms per cm^3 .

Claim 3. (Original).

The process as claimed in claim 1,
wherein the traveling magnetic field exerts a force on the
melt which is primarily directed vertically downward at the
crucible wall.

Claim 4. (Original).

The process as claimed in claim 1,
wherein the traveling magnetic field exerts a force on the
melt which is primarily directed vertically upward at the
crucible wall.

Claim 5. (Cancelled).

Claim 6.. (Cancelled).

Claim 7. (Cancelled).

Claim 8. (Cancelled).

Claim 9. (Cancelled).

Claim 10. (Cancelled).

Claim 11. (Cancelled).

Claim 12. (Cancelled).

Claim 13. (Cancelled).

Claim 14. (Currently Amended).

A process for producing a silicon single crystal, comprising pulling a silicon single crystal from a silicon melt which is contained in a crucible having a crucible wall and having a crucible diameter of at least 450 mm,

placing a heat shield above said crucible; and said silicon single crystal being pulled with a diameter of at least 200 mm; and

exposing the silicon melt to an influence of a traveling magnetic field which exerts a substantially vertically oriented force on the melt in a region of the crucible wall; and

the magnetic field is due to three coils which are connected to a 3-phase power supply, and the traveling magnetic field which, in the region of the crucible wall, exerts a substantially

vertically oriented force on the melt is generated by suitable selection of an order of connections; and the connections of the coils have a phase angle in an order 0° - 60° - 120° or 0° - 120° - 240° , except for said traveling magnetic field no further magnetic field being applied to the melt.

Claim 15. (New).

A process for producing a silicon single crystal, consisting of the steps of

pulling a silicon single crystal from a silicon melt which is contained in a crucible having a crucible wall and having a crucible diameter of at least 450 mm,

placing a heat shield above said crucible; and said silicon single crystal being pulled with a diameter of at least 200 mm; and

exposing the silicon melt to an influence of a traveling magnetic field which exerts a substantially vertically oriented force on the melt in a region of the crucible wall, to produce attenuation of low frequency temperature fluctuations.

Claim 16. (New).

A process for producing a silicon single crystal, consisting of the steps of

pulling a silicon single crystal from a silicon melt which

is contained in a crucible having a crucible wall and having a crucible diameter of at least 450 mm,

placing a heat shield above said crucible; and said silicon single crystal being pulled with a diameter of at least 200 mm; and

exposing the silicon melt to an influence of a traveling magnetic field which exerts a substantially vertically oriented force on the melt in a region of the crucible wall, to produce attenuation of low frequency temperature fluctuations; and

the magnetic field is due to three coils which are connected to a 3-phase power supply, and the traveling magnetic field which, in the region of the crucible wall, exerts a substantially vertically oriented force on the melt is generated by suitable selection of an order of connections; and the connections of the coils have a phase angle in an order $0^\circ - 60^\circ - 120^\circ$ or $0^\circ - 120^\circ - 240^\circ$.